

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A light-emitting device comprising:

- a transistor formed over a substrate;
- a first passivation film and a second passivation film;
- a light-emitting element formed between the first passivation film and the second passivation film; and
- a wiring formed over the first passivation film and connected to the transistor,

wherein the light-emitting element comprises an anode, a cathode and a light-emitting layer between the anode and the cathode;

wherein the wiring is in contact with the anode on the first passivation film;

- wherein the anode is in contact with the first passivation film;
- wherein the cathode is in contact with the second passivation film;
- wherein the light-emitting layer comprises a dopant at a concentration of 0.1 % by weight or more and 0.4 % by weight or less.

2. (Currently Amended) A light-emitting device comprising:

- a transistor formed over a substrate;
- a first passivation film and a second passivation film;
- a photosensitive organic resin film having an opening;

a light-emitting element having an anode, a cathode and a light-emitting layer between the anode and the cathode ; and

a wiring formed over the first passivation film connected to the transistor,

wherein the light-emitting layer comprises a dopant at a concentration of 0.1 % by weight or more and 0.4 % by weight or less;

wherein the wiring is in contact with the anode on the first passivation film;

wherein the anode and the photosensitive organic resin film are in contact with the first passivation film;

wherein the cathode is in contact with the second passivation film;

wherein the anode, the cathode and the light-emitting layer are overlapped in the opening,

wherein the photosensitive organic resin film and the cathode are covered with the second passivation film.

3. (Original) A light-emitting device according to claim 2, wherein a radius of curvature of a curve that a section in the opening of the photosensitive organic resin film depicts is in the range of from 0.2 to 2 μ m.

4. (Original) A light-emitting device according to claim 2, wherein the photosensitive organic resin film has positive photosensitivity.

5. (Original) A light-emitting device according to claim 2, wherein the photosensitive organic resin film has negative photosensitivity.

6. (Original) A light-emitting device according to any one of claims 1 and 2, wherein at least one of the first passivation film and the second passivation film is a carbon nitride film or a silicon nitride film formed by an RF sputtering process.

7. (Original) A light-emitting device according to any one of claims 1 and 2, wherein at least one of the first passivation film and the second passivation film comprises a material selected from the group consisting of DLC, boron nitride and alumina.

8. (Previously Presented) A electronic equipment having the light-emitting device according to claim 1 and 2,

wherein the electronic equipment is selected from the group consisting of video cameras, digital cameras, goggle type displays, navigation systems, audio reproducing devices, laptop computers, game machines, portable information terminals, image reproducing device.

9. (Original) A light-emitting device according to any one of claims 1 and 2,

wherein the light-emitting element, after turning on for 100 hr with an initial intrinsic brightness set at 320 cd/mm^2 and a duty ratio set at 70 %, has a diminishing amount of the intrinsic brightness of substantially 10 % or less of the initial intrinsic brightness.

10. (Original) A light-emitting device according to any one of claims 1 and 2,
wherein the light-emitting element, after turning on for 1000 hr with an initial intrinsic brightness set at 320 cd/mm^2 and a duty ratio set at 70 %, has a diminishing amount of the intrinsic brightness of substantially 20 % or less of the initial intrinsic brightness.

11. (Previously Presented) A light-emitting device according to any one of claims 1 and 2,

wherein the transistor controls a current that is supplied to the light-emitting element,

wherein both the light-emitting element and the transistor are plurally disposed in a pixel portion of the light-emitting device,

wherein the pixel portion is disposed on a substrate, and

wherein when brightness of the light-emitting element is set at 200 nt when a duty ratio is set at 70 %, a temperature of a portion that overlaps with the pixel portion of the substrate is 40 degree centigrade or less.

12. (Previously Presented) A light-emitting device according to any one of claims 1 and 2,

wherein the transistor controls a current that is supplied to the light-emitting element,

wherein both the light-emitting element and the transistor are plurally disposed in a pixel portion of the light-emitting device,

wherein the pixel portion is disposed on a substrate,

wherein when power consumption of the light-emitting element and the transistor is set at 600 mW when a duty ratio is set at 70 %, a temperature of a portion that overlaps with the pixel portion of the substrate is 40 degree centigrade or less.

13. (Previously Presented) A light-emitting device as set forth in any one of claims 1 and 2,

wherein the transistor controls a current that is supplied to the light-emitting element;

both the light-emitting element and the transistor are plurally disposed in a pixel portion of the light-emitting device; and

the pixel portion is disposed on a substrate;

wherein when brightness of the light-emitting element is set at 130 nt when a duty ratio is set at 70 %, a temperature of a portion that overlaps with the pixel portion of the substrate is 35 degree centigrade or less.

14. (Previously Presented) A light-emitting device according to any one of claims 1 and 2,

wherein the transistor controls a current that is supplied to the light-emitting element,

wherein both the light-emitting element and the transistor are plurally disposed in a pixel portion of the light-emitting device,

wherein the pixel portion is disposed on a substrate, and

wherein when power consumption of the light-emitting element and the transistor is set at 400 mW when a duty ratio is set at 70 %, a temperature of a portion that overlaps with the pixel portion of the substrate is 35 degree centigrade or less.

15. (Previously Presented) A light-emitting device according to any one of claims 1 and 2,

wherein the light-emitting layer comprises a quinacridone derivative.

16-22 (Canceled).

23. (New) A light-emitting device comprising:

a transistor formed over a substrate;

a first passivation film and a second passivation film;

a light-emitting element formed between the first passivation film and the second passivation film; and

a wiring formed over the first passivation film and connected the transistor,

wherein the light-emitting element comprises an anode, a cathode and a light-emitting layer between the anode and the cathode,

wherein the wiring is in contact with the anode on the first passivation film,

wherein the anode is in contact with the first passivation film, and

wherein the cathode is in contact with the second passivation film.